

Phase-Cut Dimmable High Side Buck LED Driver with High Power Factor

General Description

The RT8413 integrates a power MOSFET and a Boundary mode controller. The RT8413 supports phase-cut dimmers, including leading-edge (TRIAC) and trailing-edge dimmers. It is used for buck converter and can be compatible with TRIAC dimmer. The driver can control the internal MOSFET and regulate output current precisely.

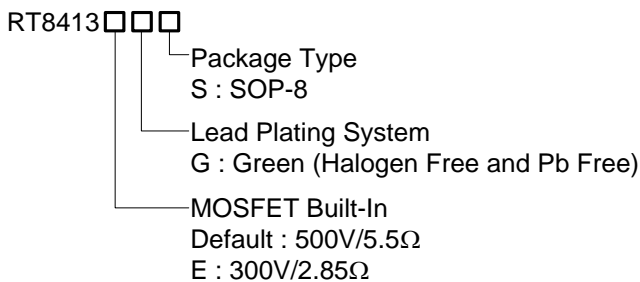
The RT8413 features a ZCS detector which keeps system operating in BCM and obtaining excellent power efficiency, better EMI performance.

The robust dimming control method can adjust the output current following the TRIAC turn on angle and avoid abnormal flicker.

This driver can use a cheap simple drum core inductor in the system instead of an EE core to obtain high efficiency.

The RT8413 is housed in a SOP-8 package. Thus, the components in the whole LED driver system can be made very compact.

Ordering Information



Note :

Richtek products are :

- ▶ RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- ▶ Suitable for use in SnPb or Pb-free soldering processes

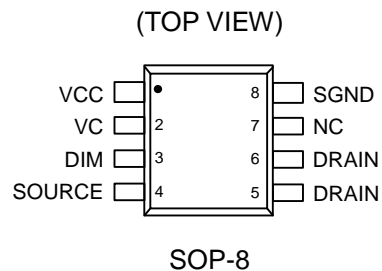
Features

- Built-In Power MOSFET
- Active Power Factor Correlation
- Programmable Constant LED Current with High-Precision Current Regulation
- Excellent Line And Load Regulation
- Suit For High Side Buck Low BOM Cost Requirement
- Unique Dimming Control Method to be Compatible with TRIAC Dimmer
- Used in Low Input Voltage Range
- Support Low Percentage Dimming Angle
- Built-in Over Thermal Protection
- Output LED String Open Protection
- Output LED String Short Protection
- Over Current Protection

Applications

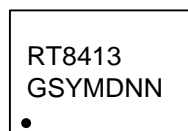
- E27, PAR, Light Bar, Offline LED Lights

Pin Configuration



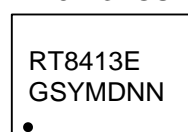
Marking Information

RT8413GS



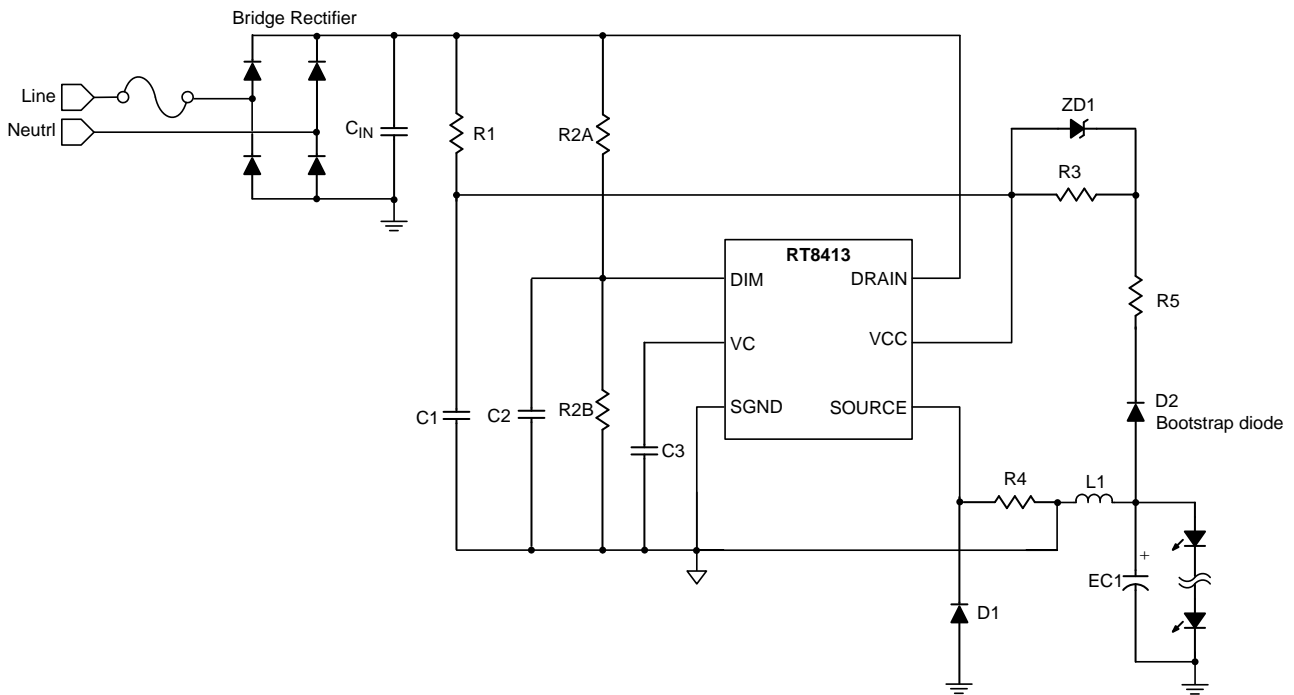
RT8413GS : Product Number
YMDNN : Date Code

RT8413EGS



RT8413EGS : Product Number
YMDNN : Date Code

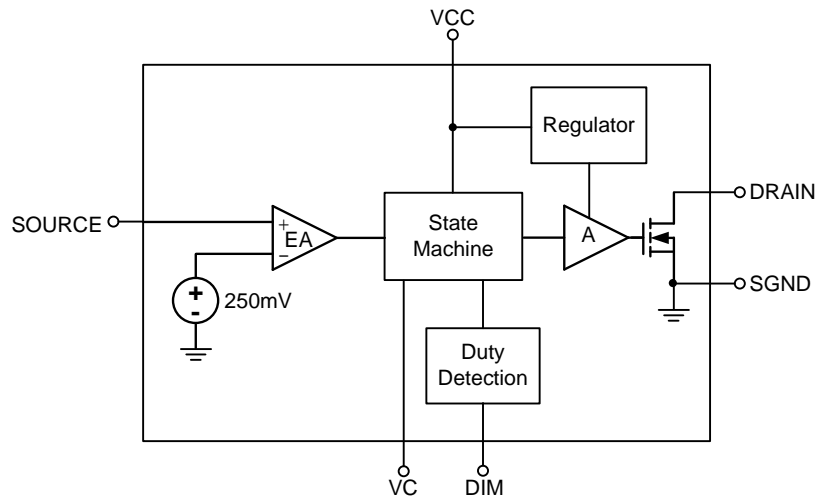
Simplified Application Circuit



Functional Pin Description

Pin No.	Pin Name	Pin Function
1	VCC	Supply voltage input of the chip. For good bypass, a ceramic capacitor near the VCC pin is required.
2	VC	Close loop compensation node.
3	DIM	Internal dimming function.
4	SOURCE	Internal power MOSFET source connection.
5, 6	DRAIN	Internal power MOSFET drain connection.
7	NC	No internal connection.
8	SGND	Ground of the chip.

Functional Block Diagram



Operation

The RT8413 senses the average output current and regulates the current precisely. The VC pin is the stability compensation node in this close loop. To stabilize the system and achieve better PFC / THDi, proper selection of a compensation network is needed.

By using boundary mode control, it provides good efficiency performance. The dimming characteristic can be optimized by adjusting the external setting of DIM pin.

Absolute Maximum Ratings (Note 1)

- VCC Supply Voltage, VCC ----- 40V
- VC, DIM, SOURCE to SGND Voltage----- -0.3V to 6V
- DRAIN to SOURCE Voltage, VDS, (RT8413) ----- -0.3V to 500V
- DRAIN to SOURCE Voltage, VDS, (RT8413E) ----- -0.3V to 300V
- Power Dissipation, P_D @ T_A = 25°C
 - SOP-8----- 0.48W
- Package Thermal Resistance (Note 2)
 - SOP-8, θ_{JA}----- 206.9°C/W
 - SOP-8, θ_{JC}----- 47°C/W
- Lead Temperature (Soldering, 10 sec.)----- 260°C
- Junction Temperature----- 150°C
- Storage Temperature Range----- -65°C to 150°C
- ESD Susceptibility (Note 3)
 - HBM (Human Body Model) ----- 2kV

Recommended Operating Conditions (Note 4)

- VCC Supply Voltage----- 10V to 30V
- Ambient Temperature Range----- -40°C to 85°C
- Junction Temperature Range ----- -40°C to 125°C

Electrical Characteristics

(V_{CC} = 24V, T_A = 25°C, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
VCC UVLO ON	V _{UVLO_ON}		17	18	19	V	
VCC UVLO OFF	V _{UVLO_OFF}		6	6.8	7.6	V	
VCC Shutdown Current	I _{SD}	V _{CC} = V _{UVLO_ON} - 3V	--	--	2	μA	
VCC Operating Current	I _{CC}	By C _{GATE} = 1nF, V _{CC} = 24V V _C = 1V, SENSE = 0V	RT8413	0.7	1.4	2.1	mA
			RT8413E	0.4	1.1	1.8	
VCC 30V Operating Current	I _{CC}	By C _{GATE} = 1nF, V _{CC} = 30V V _C = 1V, SENSE = 0V	RT8413	1.6	2.3	3	mA
			RT8413E	1.3	2	2.7	
VCC OVP Level	V _{OVP}		34.5	37	39.5	V	
VCC Clamp Level	V _{CC_CLAMP}		--	29	--	V	
VCC Clamp Current	I _{CC_CLAMP}		--	0.85	--	mA	
Sense Pin Leakage Current	I _{SENSE}	V _{SENSE} = 3V	--	1	2	μA	
Current Sense Threshold	V _{SENSE}		240	250	260	mV	
DIM Pin Leakage Current	I _{DIM}	V _{DIM} = 5V	--	--	1	μA	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 12V, I _D = 50mA	RT8413	--	5.5	--	Ω
			RT8413E	--	2.85	--	
Drain-Source Leakage Current	I _{DSS}	RT8413, V _{DS} = 500V	--	--	10	μA	
		RT8413E, V _{DS} = 300V					

Note 1. Stresses beyond those listed “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Note 2. θ_{JA} is measured under natural convection (still air) at T_A = 25°C with the component mounted on a low effective-thermal-conductivity two-layer test board on a JEDEC thermal measurement standard. θ_{JC} is measured at the exposed pad of the package.

Note 3. Devices are ESD sensitive. Handling precaution recommended.

Note 4. The device is not guaranteed to function outside its operating conditions

Typical Application Circuit

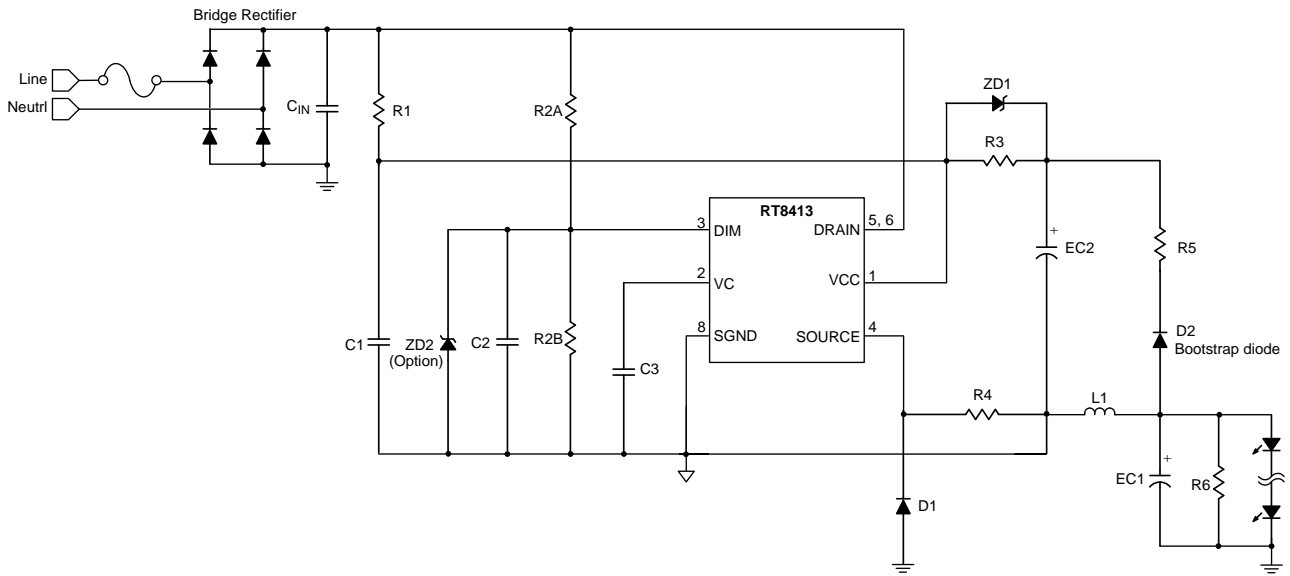
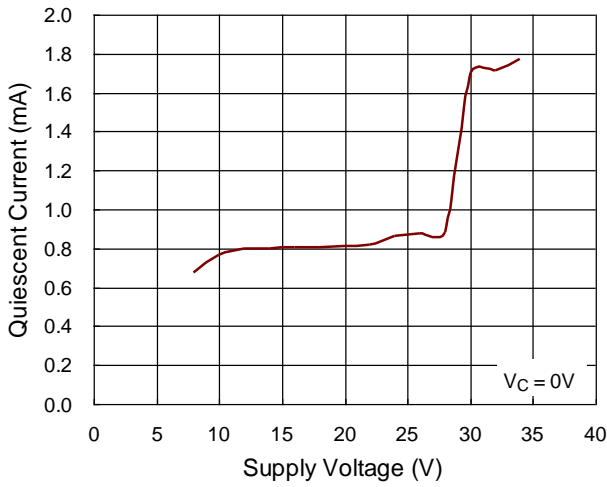


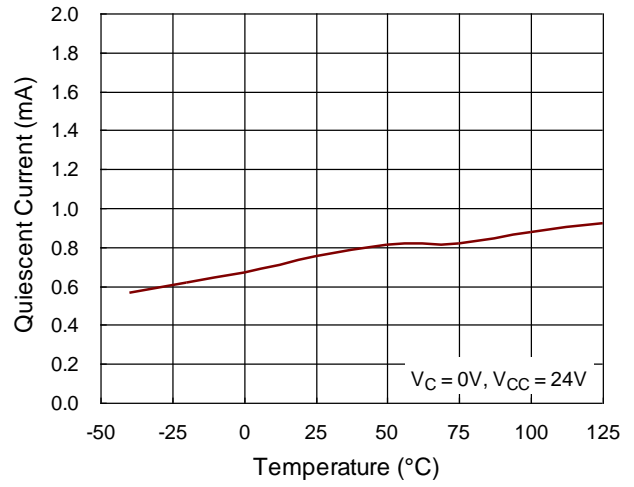
Figure 1. Typical Application of Buck Type

Typical Operating Characteristics

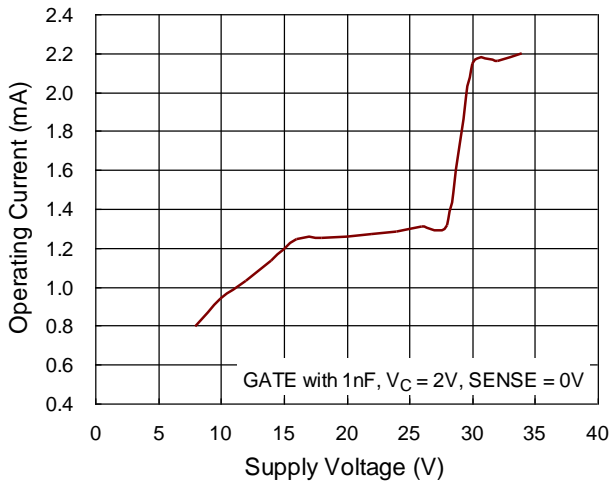
Quiescent Current vs. Supply Voltage



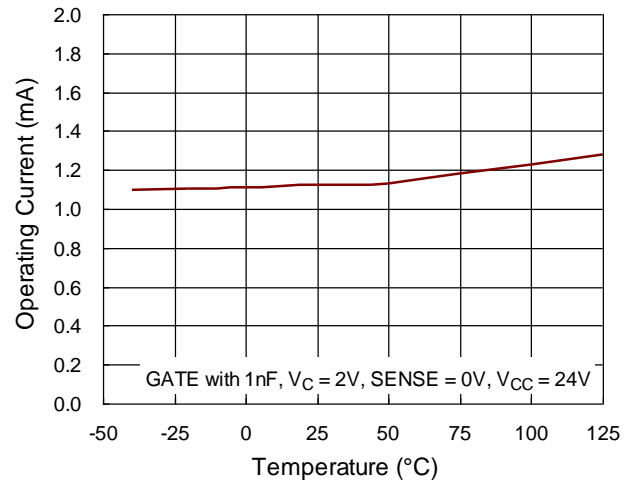
Quiescent Current vs. Temperature



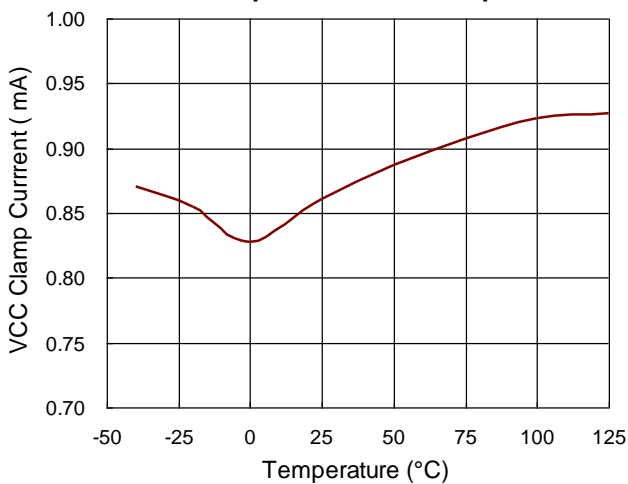
Operating Current vs. Supply Voltage



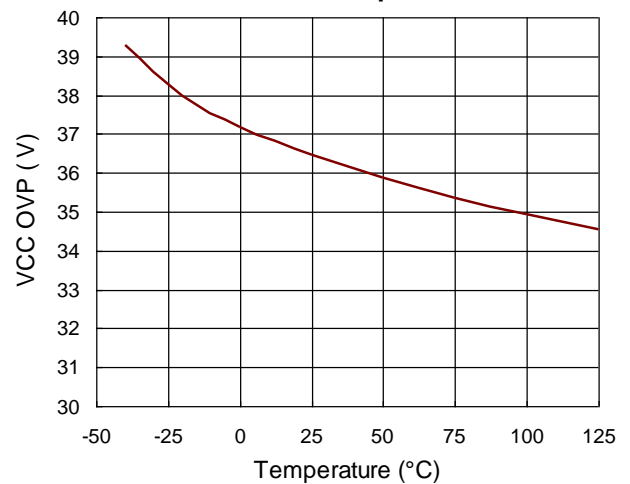
Operating Current vs. Temperature



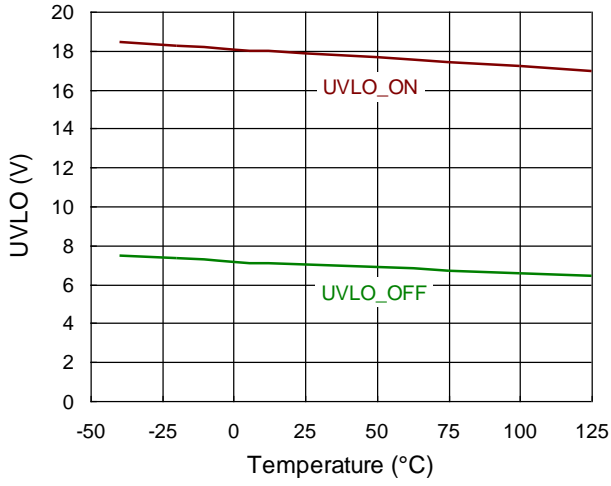
VCC Clamp Current vs. Temperature



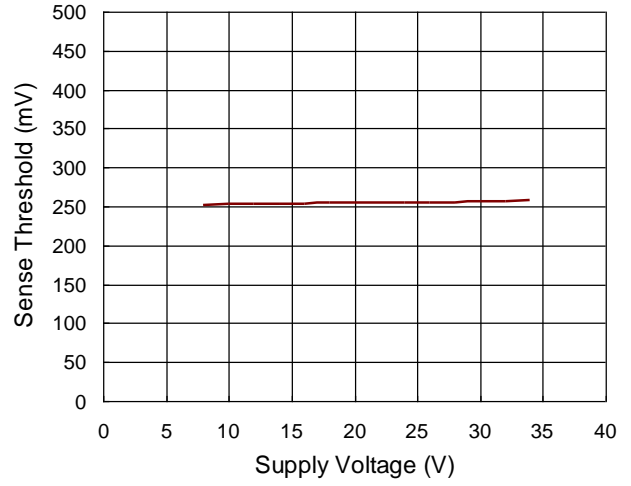
OVP vs. Temperature



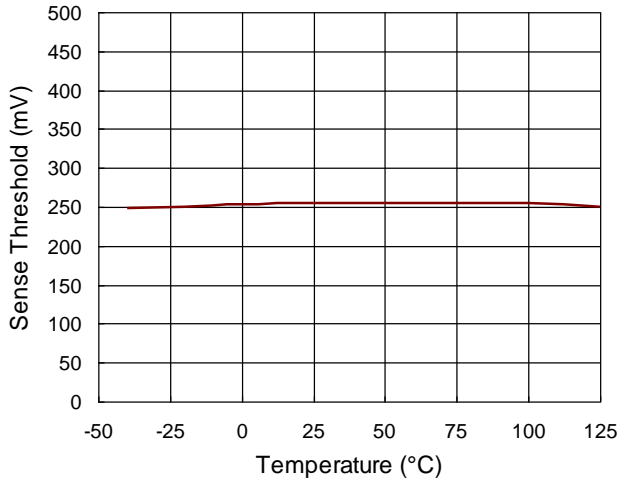
UVLO vs. Temperature



Sense Threshold vs. Supply Voltage



Sense Threshold vs. Temperature



Application Information

The RT8413 integrates a power MOSFET and housed in a SOP-8 package. Thus, the components in the whole LED driver system can be made very compact.

The RT8413 can achieve high accuracy LED output current via the average current feedback loop control. The internal sense voltage (250mV typ.) is used to set the average output current. The average current is set by the external resistor, RS. The sense voltage is also used for over current protection (OCP) function. The typical OCP threshold is about seven times of the sense voltage threshold.

Under Voltage Lockout (UVLO)

The RT8413 includes a UVLO function with 11.2V hysteresis. For system start up, the VIN must rise over 18V (typ.) to turn on the internal MOSFET. The internal MOSFET will turn off if VIN falls below 6.8V (typ.)

Setting Average Output Current

The output current that flows through the LED string is set by an external resistor, RS, which is connected between the SGND and SOURCE pins. The relationship between output current, IOUT, and RS is shown below :

$$I_{OUT} = \frac{250}{R_S}(\text{mA})$$

Start-up Resistor

The start-up resistor should be chosen to set the start up current exceeds certain minimum value. Otherwise, the RT8413 may latch off and the system will never start.

The start-up current equals $(\sqrt{2} \times 90V) / R1$ (for 110VAC regions), and equals $(\sqrt{2} \times 180V) / R1$ (for 220VAC regions). The typical required minimum start-up current is 100µA. The typical total start up resistance (R1) is around 1M Ohm for universal inputs.

Input Diode Bridge Rectifier Selection

The current rating of the input bridge rectifier is dependent on the VOUT /VIN conversion ratio and out LED current. The voltage rating of the input bridge rectifier, VBR, on the other hand, is only dependent on the input voltage. Thus, the VBR rating is calculated as

below :

$$V_{BR} = 1.2 \times (\sqrt{2} \times V_{AC(MAX)})$$

where VAC(MAX) is the maximum input voltage (RMS) and the parameter 1.2 is used for safety margin.

For this example :

$$V_{BR} = 1.2 \times (\sqrt{2} \times V_{AC(MAX)}) = (1.2 \times \sqrt{2} \times 264) = 448V$$

If the input source is universal, VBR will reach 448V. In this case, a 600V, 0.5A bridge rectifier can be chosen.

Input Capacitor Selection

For High Power Factor application, the input Capacitor CIN should use a small value capacitance to achieve line voltage sine-wave.

The voltage rating of the input filter capacitor, VCIN, should be large enough to handle the input voltage.

$$V_{CIN} \geq (1.2 \times 2 \times V_{AC(MAX)}) = (1.2 \times 2 \times 264) = 448V$$

Thus, a 0.1µF / 500V film capacitor can be chosen in this case.

Inductor Selection

For high power factor application, the RT8413 operates the converter in BCM (Boundary-Condition Mode). The inductance range is defined by peak current of inductor, maximum and minimum value of switching on time and off time, for ensuring the inductor operates in BCM. The peak current of inductor is showed as below :

$$I_{PEAK} = \frac{2P_{in}}{V_{PEAK}F(a)}$$

where $a = \frac{V_{OUT}}{V_{PEAK}}$

and

$$F(a) \approx -0.411a^4 + 0.296a^3 - 0.312a^2 + 0.638a - 0.0000846, \{a|0 \sim 0.7\}$$

The inductance range is showed as below :

$$L = \frac{V_{OUT}T_{OFF}}{I_{PEAK}} = \frac{(V_{PEAK} - V_{OUT})T_{ON}}{I_{PEAK}}$$

Where $0.5\mu s \leq T_{ON} \leq 35\mu s$ (typ.) and $5\mu s \leq T_{OFF} \leq 35\mu s$ (typ.).

The frequency at the top of the sine wave can be calculated :

$$f_{SW} = \frac{1}{T_{ON} + T_{OFF} + T_{DELAY}}$$

T_{DELAY} is about 0.6 μ s (typ.).

Forward Diode Selection

When the power switch turns off, the path for the current is through the diode connected between the switch output and ground. This forward biased diode must have minimum voltage drop and recovery time. The reverse voltage rating of the diode should be greater than the maximum input voltage and the current rating should be greater than the maximum load current.

The peak voltage stress of diode is :

$$V_D \geq 1.2 \times (\sqrt{2} \times V_{AC(MAX)}) = 1.2 \times (\sqrt{2} \times 264) = 448V$$

The input source is universal ($V_{IN} = 85V$ to $264V$), V_D will reach 448V.

Thermal Protection (OTP)

A thermal protection feature is included to protect the RT8413 from excessive heat damage. When the junction temperature exceeds a threshold of 150°C (typ.), the thermal protection OTP will be triggered and the internal MOSFET will be turned off.

Thermal Considerations

The junction temperature should never exceed the absolute maximum junction temperature $T_{J(MAX)}$, listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula :

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance, θ_{JA} , is highly package dependent.

For a SOP-8 package, the thermal resistance, θ_{JA} , is 206.9°C/W on a standard JEDEC low effective-thermal-conductivity two-layer test board. The maximum power dissipation at $T_A = 25^\circ C$ can be calculated as below :

$$P_{D(MAX)} = (125^\circ C - 25^\circ C) / (206.9^\circ C/W) = 0.48W \text{ for a SOP-8 package.}$$

The maximum power dissipation depends on the operating ambient temperature for the fixed $T_{J(MAX)}$ and the thermal resistance, θ_{JA} . The derating curves in Figure 2 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

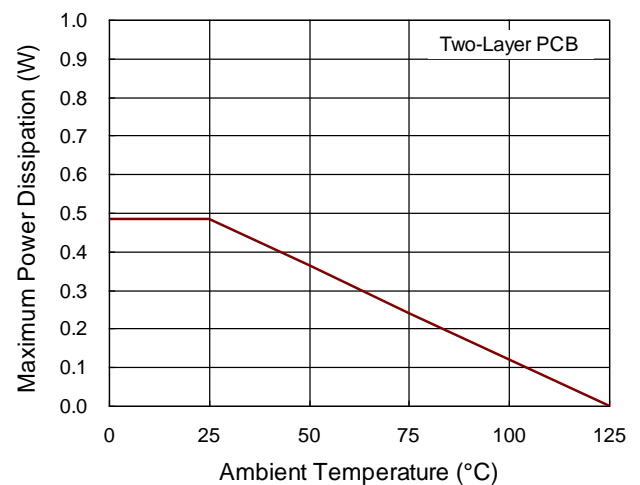


Figure 2. Derating Curve of Maximum Power Dissipation

Layout Considerations

For best performance of the RT8413, the following layout guidelines should be strictly followed.

The hold up capacitor, C1, must be placed as close as possible to the VCC pin.

The compensation capacitor, C2 and C3, must be placed as close as possible to the VC and the DIM pin.

The IC SOURCE pin are high frequency switching nodes. The traces must be as wide and short as possible.

Keep the main traces with switching current as short and wide as possible.

Place CIN, L1, R4, EC1, and D1 as close to each other as possible.

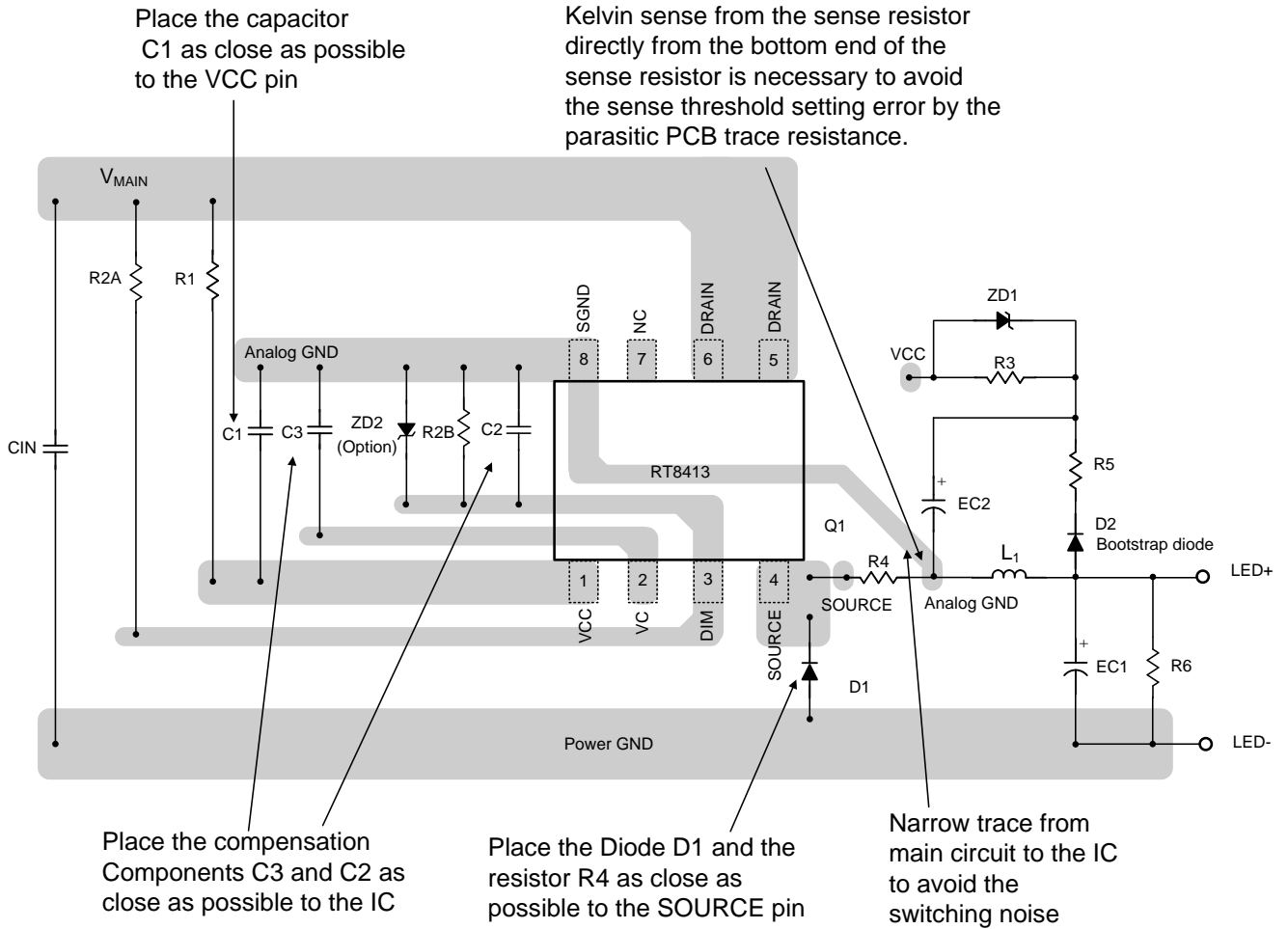
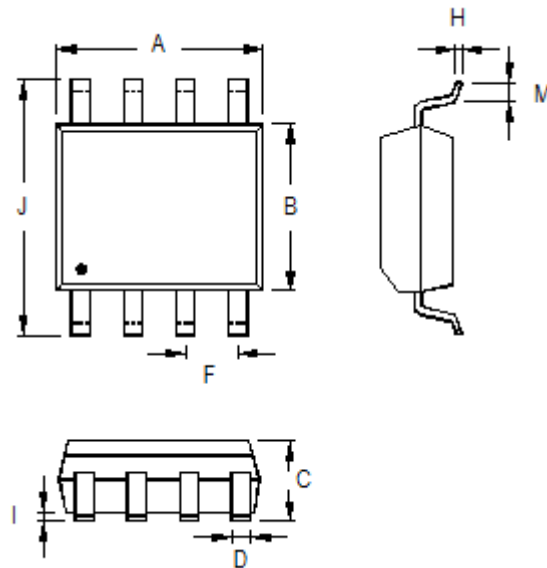


Figure 3. PCB Layout Guide

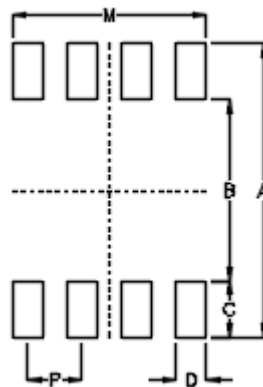
Outline Dimension



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.801	5.004	0.189	0.197
B	3.810	3.988	0.150	0.157
C	1.346	1.753	0.053	0.069
D	0.330	0.508	0.013	0.020
F	1.194	1.346	0.047	0.053
H	0.170	0.254	0.007	0.010
I	0.050	0.254	0.002	0.010
J	5.791	6.200	0.228	0.244
M	0.400	1.270	0.016	0.050

8-Lead SOP Plastic Package

Footprint Information



Package	Number of Pin	Footprint Dimension (mm)						Tolerance
		P	A	B	C	D	M	
SOP-8	8	1.27	6.80	4.20	1.30	0.70	4.51	±0.10

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